Table II - Electrical Characteristics for Qual Samples						
Parameter	**Symbol**	**Conditions**	**Sub-groups**	**Limit Min**	**Limit Max**	**Units**
V_S = +5V, V_{CM} = 2.5V						
Input Offset Voltage	V_{OS}		1		200	µV
			2, 3		400	
		M, D, L, R_3/	1		600	
Input Offset Current	I_{OS}	1/	1, 2, 3		50	nA
		M, D, L, R_3/	1		400	
Input Bias Current	I_B	1/	1		350	
			2, 3		575	
		M, D, L, R_3/	1		3000	
Common Mode Rejection Ratio 4/	CMRR	V_{CM} = 1V to 4V	1, 2, 3	86		dB
Output High Voltage 4/	V_{OH}	I_L = 1mA	4	4.8		V
Output Low Voltage 4/	V_{OL}	I_L = 1mA	4		125	mV
Large Signal Voltage Gain	A_{VO}	$R_L \geq 2k\Omega$, V_{OUT} = 1V to 4V	4	50		V/mV
			5, 6	25		
		$R_L \geq 10k\Omega$, V_{OUT} = 1V to 4V, M, D, L, R_3/	4	25		
Supply Current 2/	I_{SY}	V_{OUT} = 2.5V	1		5.8	mA
		M, D, L, R_3/	1		5.85	
V_S = ±15V, V_{CM} = 0V						
Input Offset Voltage 4/	V_{OS}		1		250	µV
			2, 3		500	
Average Input Offset Voltage Drift 4/	TCV_{OS}		8		2.5	µV/°C
Input Offset Current 4/	I_{OS}		1, 2, 3		50	nA
Input Bias Current 4/	I_B		1		350	nA
			2, 3		575	
Common Mode Rejection Ratio 4/	CMRR	V_{CM} = -15V to +15V	1, 2, 3	80		dB
Power Supply Rejection Ratio 4/	PSRR	V_S = ±2V to ±18V	1, 2, 3	90		dB
Large Signal Voltage Gain 4/	A_{VO}	$R_L \geq 2k\Omega$, V_{OUT} = ±10V	4	150		V/mV
			5, 6	75		
Supply Current 2/ 4/	I_{SY}	V_{OUT} = 0V	1		8	mA
		V_S = ±18V, V_{OUT} = 0V	1, 2, 3		9	

Table II Notes:

1/ Guaranteed by V_S = ±15V test.
2/ limit = total all four amplifiers.
3/ I_{SY} Devices tested at 100Krad irradiation.
4/ Parameter not tested post irradiation.